

### ABSTRACT OF THE DISCLOSURE

Provided is a capacitor of a semiconductor device. The capacitor includes a capacitor lower electrode disposed on a semiconductor substrate. A first dielectric layer comprising aluminum oxide ( $\text{Al}_2\text{O}_3$ ) is disposed on the capacitor lower electrode. A second dielectric layer comprising a material having a higher dielectric constant than that of aluminum oxide is disposed on the first dielectric layer. A third dielectric layer comprising aluminum oxide is disposed on the second dielectric layer. A capacitor upper electrode is disposed on the third dielectric layer. The capacitor of the present invention can improve electrical properties.

5 Thus, power consumption can be reduced and capacitance per unit area is high enough to achieve high integration.

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